

CLEAN COPY OF CLAIMS:

1. (Amended) A semiconductor device comprising:
a first semiconductor chip consisting of at least either a circuit against static damage or a passive component;
a second semiconductor chip and a third semiconductor chip installed on a support substrate, wherein said second semiconductor chip and said third semiconductor chip are connected with each other through said first semiconductor chip; and
wherein said semiconductor chip is a DRAM chip, and said third semiconductor chip is a logic chip.

4. (Amended) A semiconductor device comprising:
a semiconductor chip consisting of at least either a circuit against static damage or a passive component, wherein said semiconductor chip consists of only said passive component, said passive component includes all of a resistor, a capacitor and a reactor.

9. (Amended) A semiconductor device comprising:
a plurality of semiconductor chips installed on a support substrate;
a wire connecting said plurality of semiconductor chips with each other and having a passive component function; and
wherein said wire having a passive component function has a length greater than that for linearly connecting terminals of said plurality of semiconductor chips with each other thereby forming a resistive element.

10. (Amended) A semiconductor device comprising:

- a plurality of semiconductor chips installed on a support substrate;
- a wire connecting said plurality of semiconductor chips with each other and
- having a passive component function; and
- a dummy wire fixed to a prescribed potential and arranged to be opposed to said wire at a prescribed interval, wherein said wire is combined with said dummy wire to form a capacitor.

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11. (Amended) The semiconductor device according to claim 9, wherein
said wire is formed either in a single layer or in two layers.
